

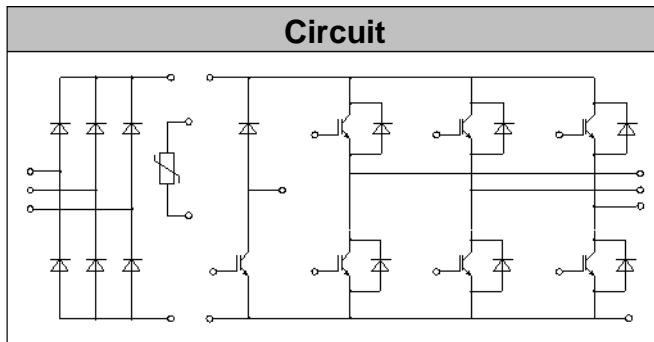


IGBT Modules

V_{CES}	1200V
I_c	10A

Applications

- Motor Drivers
- AC and DC servo drive amplifier
- UPS (Uninterruptible Power Supplies)



Features

- Low switching losses
- Low $V_{CE(sat)}$ with positive temperature coefficient
- Including fast & soft recovery anti-parallel FWD
- Low inductance case
- High short circuit capability(10us)
- Maximum junction temperature 175°C

● IGBT- inverter

Absolute Maximum Ratings

Parameter	Symbol	Conditions	Value	Unit
Collector-Emitter Voltage	V_{CES}	$V_{GE}=0V, I_c=1mA, T_{vj}=25^{\circ}C$	1200	V
Continuous Collector Current	I_c	$T_C=100^{\circ}C, T_{vjmax}=175^{\circ}C$	10	A
Repetitive Peak Collector Current	I_{CRM}	$t_p=1ms$	20	A
Gate-Emitter Voltage	V_{GES}	$T_{vj}=25^{\circ}C$	± 20	V
Total Power Dissipation	P_{tot}	$T_C=25^{\circ}C$ $T_{vjmax}=175^{\circ}C$	120	W



● IGBT- inverter

Characteristic values

Parameter	Symbol	Conditions	Value			Unit	
			Min.	Typ.	Max.		
Gate-emitter Threshold Voltage	$V_{GE(th)}$	$V_{GE}=V_{CE}, I_C=0.5mA, T_{vj}=25^{\circ}C$	5.2	6.0	6.8	V	
Collector-Emitter Cut-off Current	I_{CES}	$V_{CE}=1200V, V_{GE}=0V, T_{vj}=25^{\circ}C$			1.0	mA	
Collector-Emitter Saturation Voltage	$V_{CE(sat)}$	$I_C=10A, V_{GE}=15V, T_{vj}=25^{\circ}C$		1.85	2.60	V	
		$I_C=10A, V_{GE}=15V, T_{vj}=125^{\circ}C$		2.15			
		$I_C=10A, V_{GE}=15V, T_{vj}=150^{\circ}C$		2.25			
Gate Charge	Q_G			0.13		uC	
Input Capacitance	C_{ies}	$V_{CE}=25V, V_{GE}=0V, f=1MHz, T_{vj}=25^{\circ}C$		0.681		nF	
Reverse Transfer Capacitance	C_{res}			0.023		nF	
Gate-Emitter leakage current	I_{GES}	$V_{CE}=0V, V_{GE}=20V, T_{vj}=25^{\circ}C$			400	nA	
Turn-on Delay Time	$t_{d(on)}$	$I_C=10A, V_{CE}=600V, V_{GE}=\pm 15V, R_G=51\Omega, T_{vj}=25^{\circ}C$		72		ns	
Rise Time	t_r			33		ns	
Turn-off Delay Time	$t_{d(off)}$			100		ns	
Fall Time	t_f			337		ns	
Energy Dissipation During Turn-on Time	E_{on}			1.16		mJ	
Energy Dissipation During Turn-off Time	E_{off}			0.78		mJ	
Turn-on Delay Time	$t_{d(on)}$		$I_C=10A, V_{CE}=600V, V_{GE}=\pm 15V, R_G=51\Omega, T_{vj}=150^{\circ}C$		71		ns
Rise Time	t_r				36		ns
Turn-off Delay Time	$t_{d(off)}$			108		ns	
Fall Time	t_f			410		ns	
Energy Dissipation During Turn-on Time	E_{on}			1.35		mJ	
Energy Dissipation During Turn-off Time	E_{off}			0.91		mJ	
SC Data	I_{sc}	$t_p \leq 10\mu s, V_{GE}=15V, T_{vj}=150^{\circ}C, V_{CC}=900V, V_{CEM} \leq 1200V$			40		A



● Diode-inverter

Absolute Maximum Ratings

Parameter	Symbol	Conditions	Value	Unit
Repetitive Peak Reverse Voltage	V_{RRM}	$T_{vj}=25^{\circ}\text{C}$	1200	V
Continuous DC Forward Current	I_F		10	A
Repetitive Peak Forward Current	I_{FRM}	$t_p=1\text{ms}$	20	A
I^2t -value	I^2t	$V_R=0\text{V}, t_p=10\text{ms}, T_{vj}=125^{\circ}\text{C}$	16.0	A^2s
		$V_R=0\text{V}, t_p=10\text{ms}, T_{vj}=150^{\circ}\text{C}$	14.0	A^2s

Characteristic values

Parameter	Symbol	Conditions	Value			Unit
			Min.	Typ.	Max.	
Forward Voltage	V_F	$I_F=10\text{A}, T_{vj}=25^{\circ}\text{C}$		2.00	2.80	V
		$I_F=10\text{A}, T_{vj}=125^{\circ}\text{C}$		1.85		
		$I_F=10\text{A}, T_{vj}=150^{\circ}\text{C}$		1.80		
Recovered Charge	Q_{rr}	$I_F=10\text{A}$		0.27		μC
Peak Reverse Recovery Current	I_{rr}	$V_R=600\text{V}$ $-di_F/dt = 600\text{A}/\mu\text{s}$		11		A
Reverse Recovery Energy	E_{rec}	$T_{vj}=25^{\circ}\text{C}$		0.28		mJ
Recovered Charge	Q_{rr}	$I_F=10\text{A}$		0.38		μC
Peak Reverse Recovery Current	I_{rr}	$V_R=600\text{V}$ $-di_F/dt = 600\text{A}/\mu\text{s}$		12		A
Reverse Recovery Energy	E_{rec}	$T_{vj}=150^{\circ}\text{C}$		0.65		mJ



● IGBT-brake-chopper

Absolute Maximum Ratings

Parameter	Symbol	Conditions	Value	Unit
Collector-Emitter Voltage	V_{CES}	$V_{GE}=0V, I_C=1mA, T_{vj}=25^\circ C$	1200	V
Continuous Collector Current	I_C	$T_C=100^\circ C, T_{vjmax}=175^\circ C$	10	A
Repetitive Peak Collector Current	I_{CRM}	$t_p=1ms$	20	A
Gate-Emitter Voltage	V_{GES}	$T_{vj}=25^\circ C$	± 20	V
Total Power Dissipation	P_{tot}	$T_C=25^\circ C, T_{vjmax}=175^\circ C$	120	W

Characteristic values

Parameter	Symbol	Conditions	Value			Unit	
			Min.	Typ.	Max.		
Gate-emitter Threshold Voltage	$V_{GE(th)}$	$V_{GE}=V_{CE}, I_C=0.5mA, T_{vj}=25^\circ C$	5.2	6.0	6.8	V	
Collector-Emitter Cut-off Current	I_{CES}	$V_{CE}=1200V, V_{GE}=0V, T_{vj}=25^\circ C$			1.0	mA	
Collector-Emitter Saturation Voltage	$V_{CE(sat)}$	$I_C=10A, V_{GE}=15V, T_{vj}=25^\circ C$		1.85	2.60	V	
		$I_C=10A, V_{GE}=15V, T_{vj}=125^\circ C$		2.15			
		$I_C=10A, V_{GE}=15V, T_{vj}=150^\circ C$		2.25			
Gate Charge	Q_G			0.13		uC	
Input Capacitance	C_{ies}	$V_{CE}=25V, V_{GE}=0V, f=1MHz, T_{vj}=25^\circ C$		0.681		nF	
Reverse Transfer Capacitance	C_{res}			0.023		nF	
Gate-Emitter leakage current	I_{GES}	$V_{CE}=0V, V_{GE}=20V, T_{vj}=25^\circ C$			400	nA	
Turn-on Delay Time	$t_{d(on)}$	$I_C=10A$ $V_{CE}=600V$ $V_{GE}=\pm 15V$ $R_G=51\Omega$ $T_{vj}=25^\circ C$		72		ns	
Rise Time	t_r			33		ns	
Turn-off Delay Time	$t_{d(off)}$				100		ns
Fall Time	t_f				337		ns
Energy Dissipation During Turn-on Time	E_{on}				1.16		mJ
Energy Dissipation During Turn-off Time	E_{off}				0.78		mJ



Turn-on Delay Time	$t_{d(on)}$	$I_C=10A$ $V_{CE}=600V$ $V_{GE}=\pm 15V$ $R_G=51\Omega$ $T_{vj}=150^\circ C$	71		ns
Rise Time	t_r		36		ns
Turn-off Delay Time	$t_{d(off)}$		108		ns
Fall Time	t_f		410		ns
Energy Dissipation During Turn-on Time	E_{on}		1.35		mJ
Energy Dissipation During Turn-off Time	E_{off}		0.91		mJ
SC Data	I_{sc}		$t_p \leq 10\mu s, V_{GE}=15V, T_{vj}=150^\circ C,$ $V_{CC}=900V, V_{CEM} \leq 1200V$	40	

● Diode-Brake-Chopper

Absolute Maximum Ratings

Parameter	Symbol	Conditions	Value	Unit
Repetitive Peak Reverse Voltage	V_{RRM}	$T_{vj}=25^\circ C$	1200	V
Continuous DC Forward Current	I_F		10	A
Repetitive Peak Forward Current	I_{FRM}	$t_p=1ms$	20	A
I^2t -value	I^2t	$V_R=0V, t_p=10ms, T_{vj}=125^\circ C$	16.0	A^2s
		$V_R=0V, t_p=10ms, T_{vj}=150^\circ C$	14.0	A^2s

Characteristic values

Parameter	Symbol	Conditions	Value			Unit
			Min.	Typ.	Max.	
Forward Voltage	V_F	$I_F=10A, T_{vj}=25^\circ C$		2.00	2.80	V
		$I_F=10A, T_{vj}=125^\circ C$		1.85		
		$I_F=10A, T_{vj}=150^\circ C$		1.80		
Recovered Charge	Q_{rr}	$I_F=10A$		0.27		μC
Peak Reverse Recovery Current	I_{rr}	$V_R=600V$ $-di_F/dt = 500A/\mu s$		11		A
Reverse Recovery Energy	E_{rec}	$T_{vj}=25^\circ C$		0.28		mJ
Recovered Charge	Q_{rr}	$I_F=10A$		0.38		μC
Peak Reverse Recovery Current	I_{rr}	$V_R=600V$ $-di_F/dt = 500A/\mu s$		12		A
Reverse Recovery Energy	E_{rec}	$T_{vj}=150^\circ C$		0.65		mJ



● Diode-Rectifier

Absolute Maximum Ratings

Parameter	Symbol	Conditions	Value	Unit
Repetitive Peak Reverse Voltage	V_{RRM}	$T_{vj}=25^{\circ}C$	1600	V
Average output Current 50/60Hz, sine wave	$I_{F(AV)}$	$T_C=100^{\circ}C$	10	A
Maximum RMS Current at Rectifier Output	I_{RMSM}	$T_C=100^{\circ}C$	20	A
Surge Forward Current	I_{FSM}	$V_R=0V, t_p=10ms, T_{vj}=45^{\circ}C$	100	A
I^2t -value	I^2t	$V_R=0V, t_p=10ms, T_{vj}=45^{\circ}C$	360	A ² s

Characteristic values

Parameter	Symbol	Conditions	Value			Unit
			Min.	Typ.	Max.	
Diode Forward Voltage	V_F	$I_F=10A, T_{vj}=150^{\circ}C$		0.90		V
Reverse Current	I_R	$T_{vj}=150^{\circ}C, V_R=1600V$			1.0	mA

● NTC-Thermistor

Characteristic values

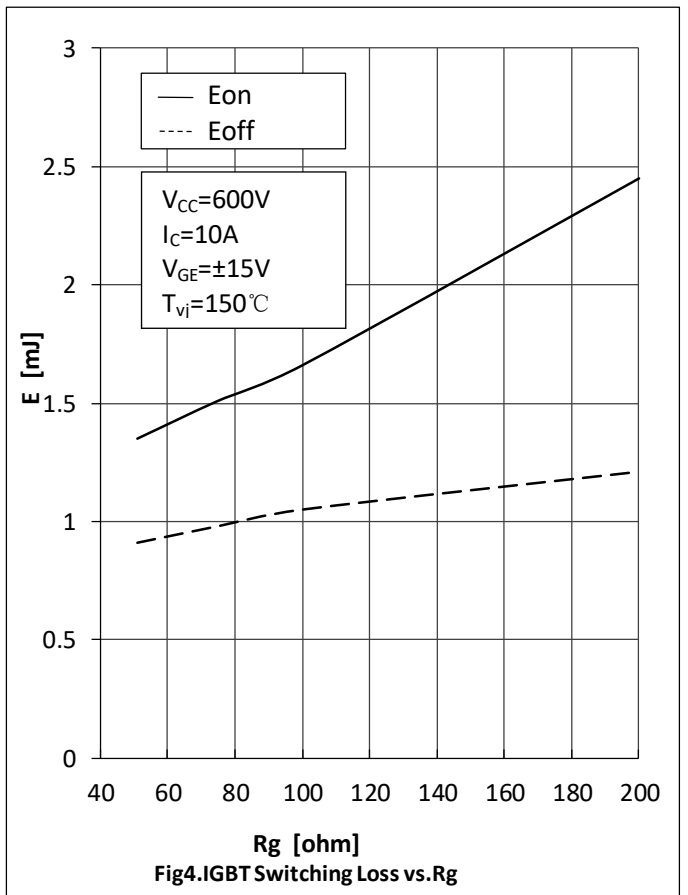
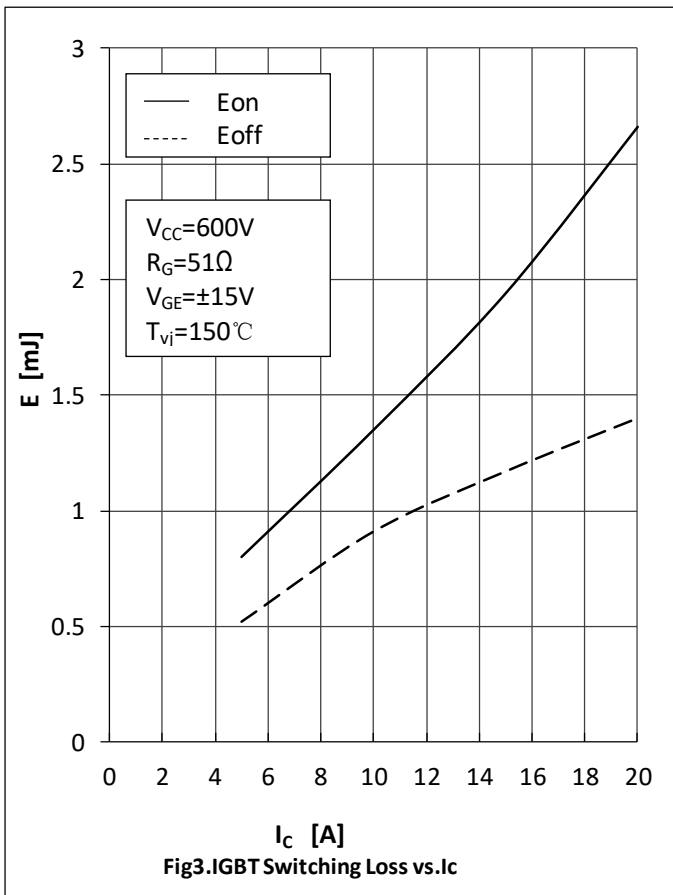
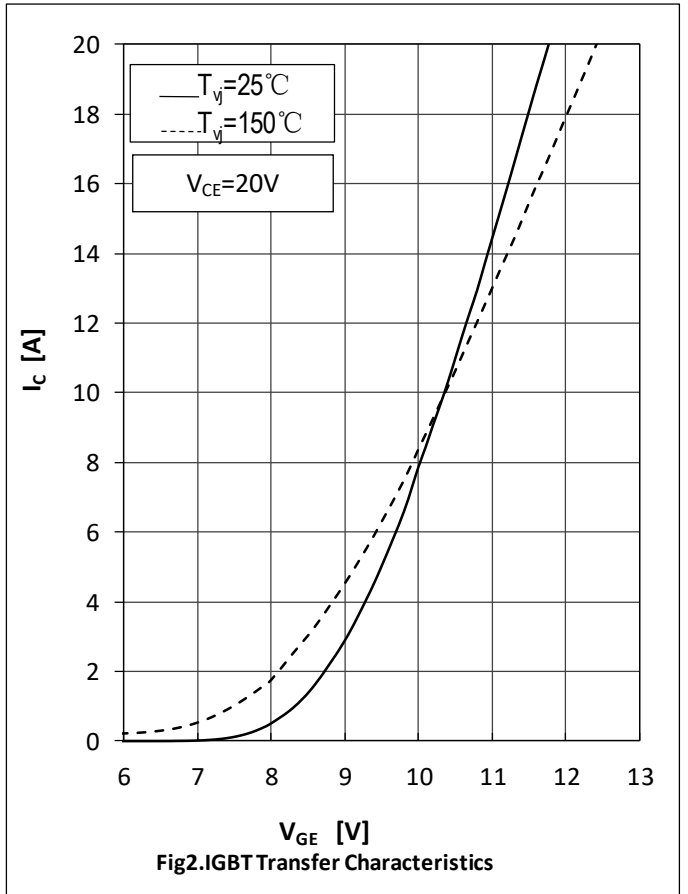
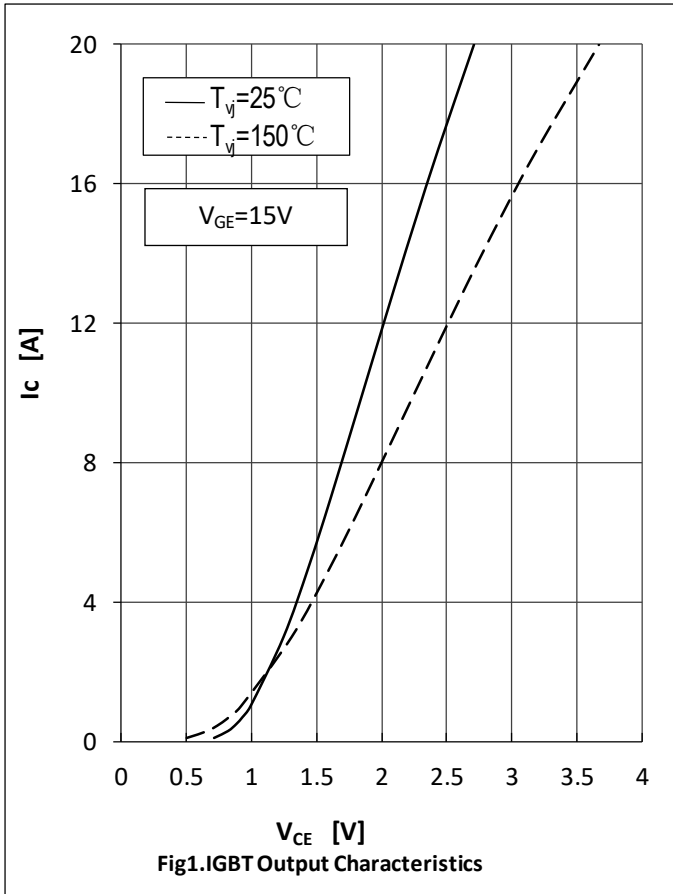
Parameter	Symbol	Conditions	Value			Unit
			Min.	Typ.	Max.	
Rated Resistance	R_{25}			5.0		k Ω
Deviation of R100	$\Delta R/R$	$T_C=100, R_{100}=493.3\Omega$	-5		5	%
Power Dissipation	P_{25}				20.0	mW
B-value	$B_{25/50}$	$R_2=R_{25}\exp[B_{25/50}(1/T_2-1/(298.15 K))]$		3375		K

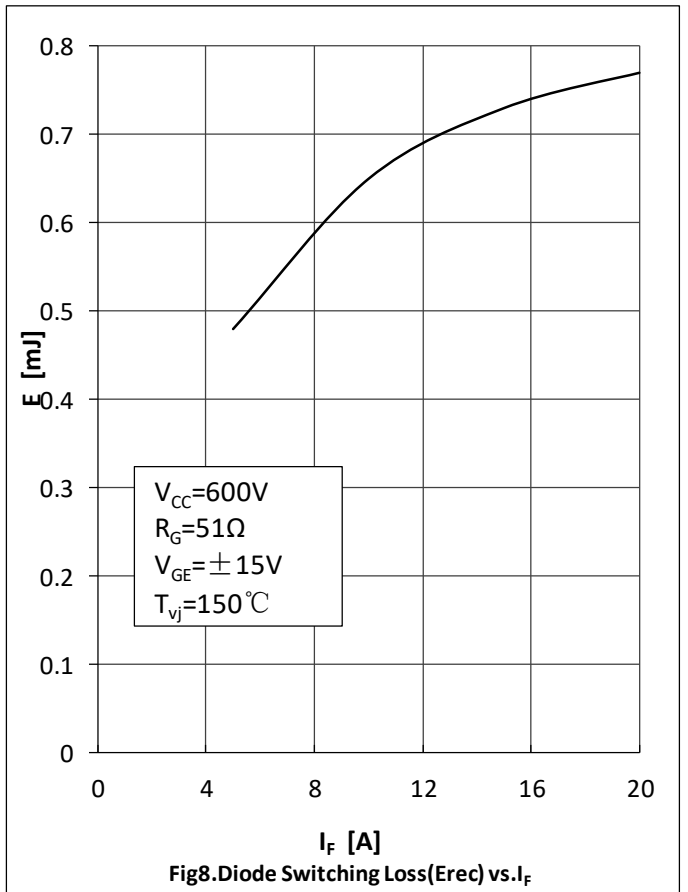
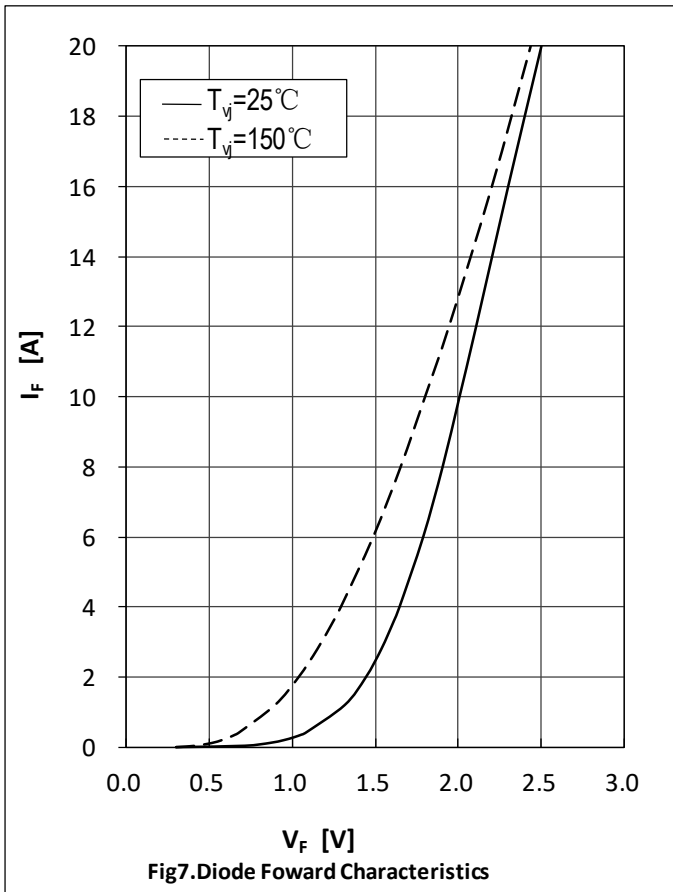
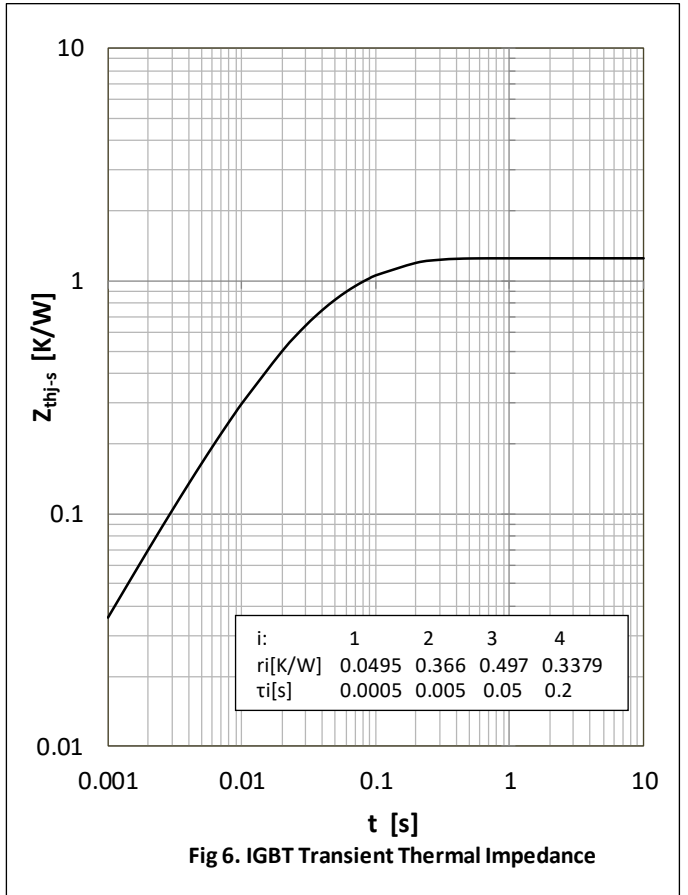
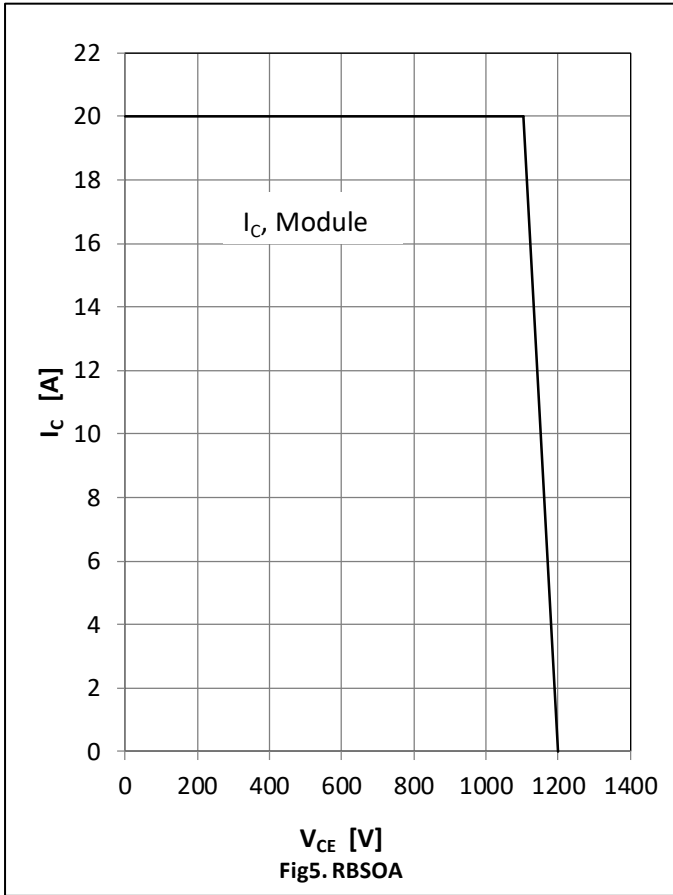


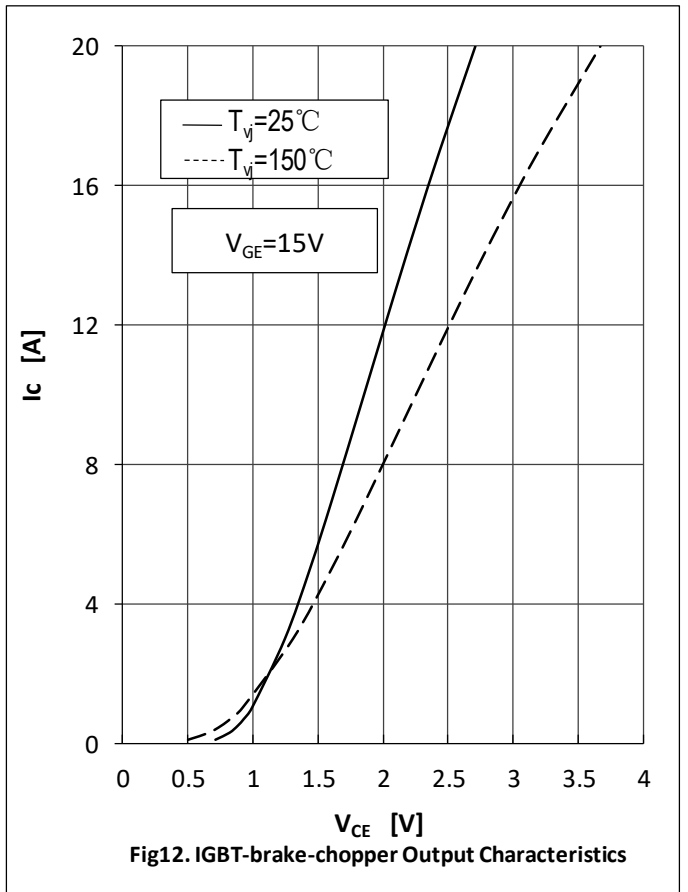
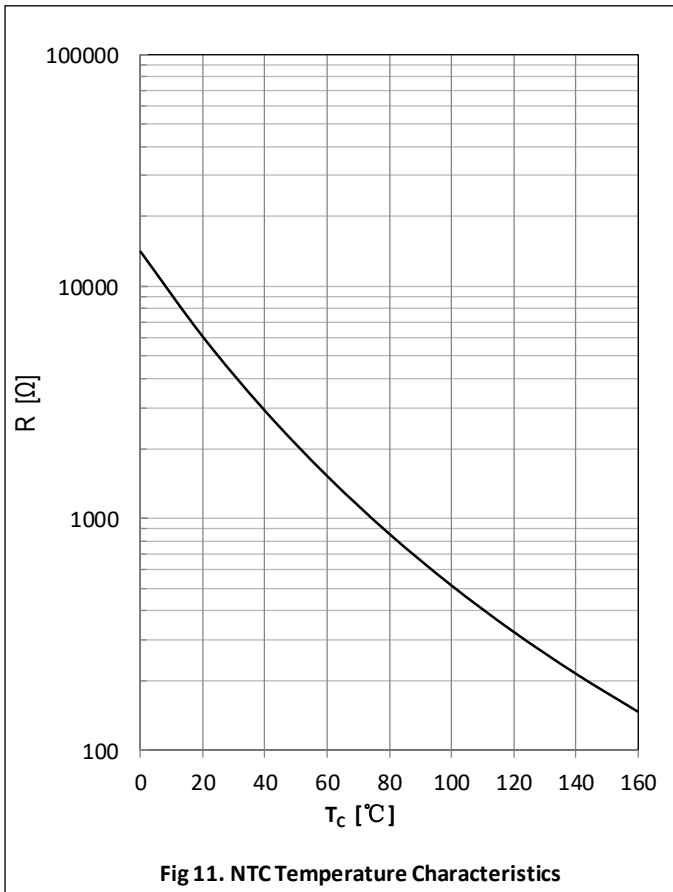
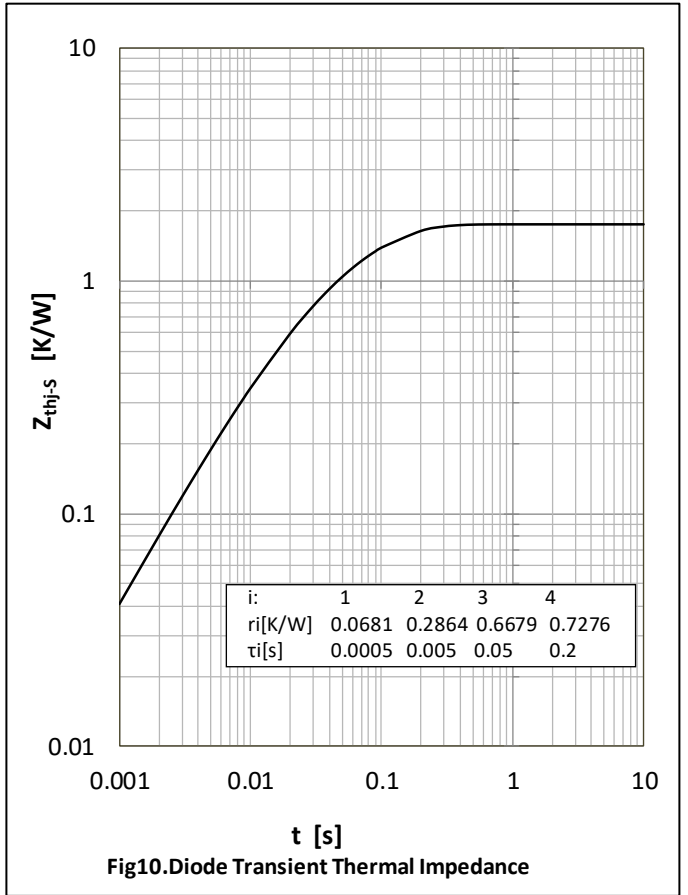
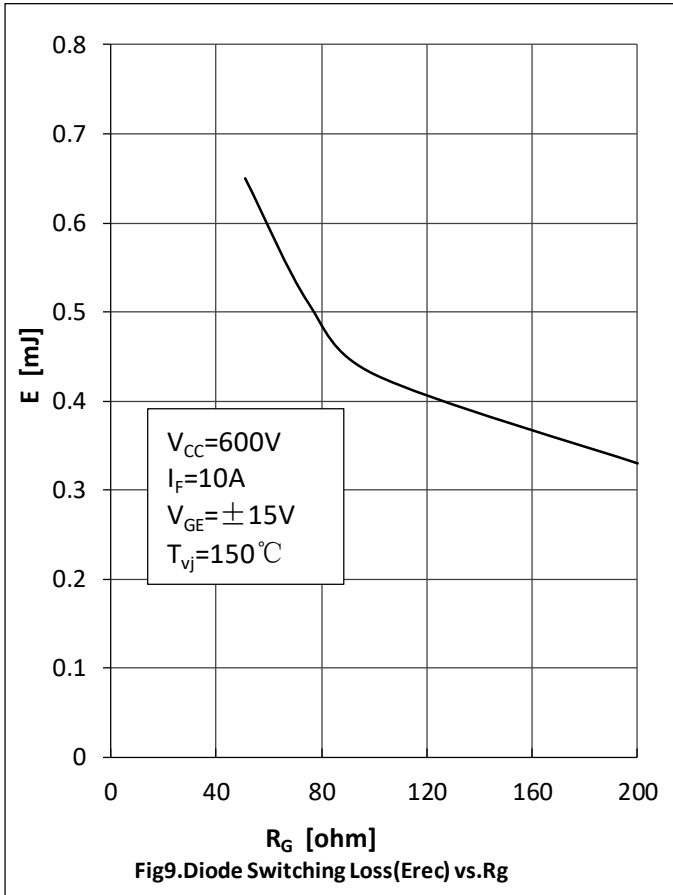
● Module Characteristics

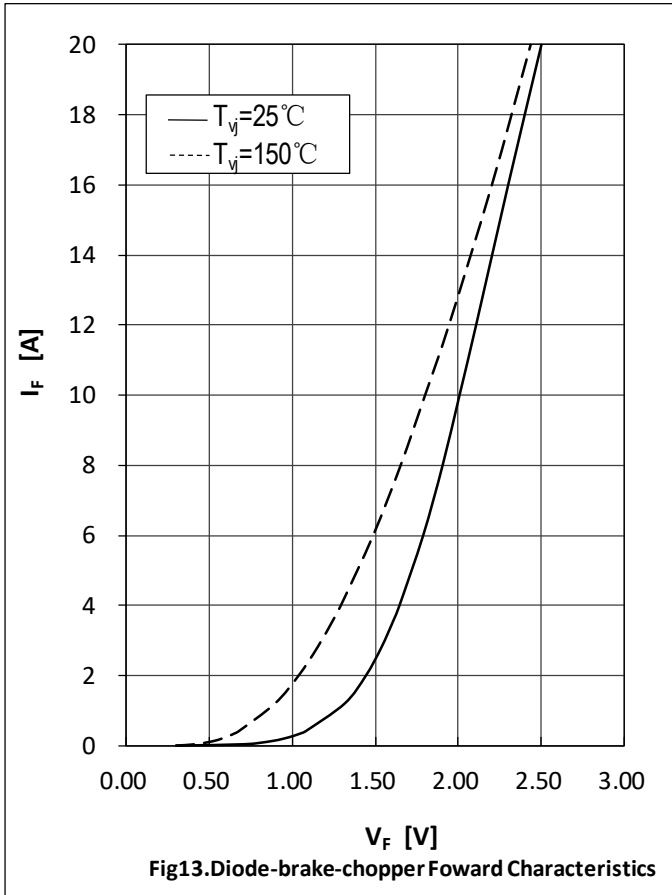
$T_C=25^{\circ}\text{C}$ unless otherwise specified

Parameter	Symbol	Conditions	Value			Unit
			Min.	Typ.	Max.	
Isolation voltage	V_{isol}	$t=1\text{min}, f=50\text{Hz}$	2500			V
Maximum Junction Temperature	T_{jmax}				175	$^{\circ}\text{C}$
Operating Junction Temperature	$T_{vj\ op}$		-40		150	$^{\circ}\text{C}$
Storage Temperature	T_{stg}		-40		150	$^{\circ}\text{C}$
Stray-inductance-module	L_{SCE}			60		nH
Module lead resistance, terminals-chip	$R_{CC'+EE}$	$T_C=25^{\circ}\text{C}$, per switch		4.0		m Ω
	$R_{AA'+CC'}$			3.0		
Thermal Resistance Junction-to Case	$R_{\theta JC}$	per IGBT-inverter		1.25		K/W
		per Diode-inverter		1.75		
		per IGBT-brake-copper		1.25		
		per Diode-chopper		1.75		
		per Diode-rectifier		2.05		
Thermal Resistance Case-to Sink	$R_{\theta CS}$	per IGBT-inverter		0.40		K/W
		per Diode-inverter		0.72		
		per IGBT-brake-copper		0.53		
		per Diode-chopper		0.77		
		per Diode-rectifier		1.10		
		per Module		0.02		
Mounting Force Per Clamp	F		3.0		6.0	N
Weight of Module	G			180		g

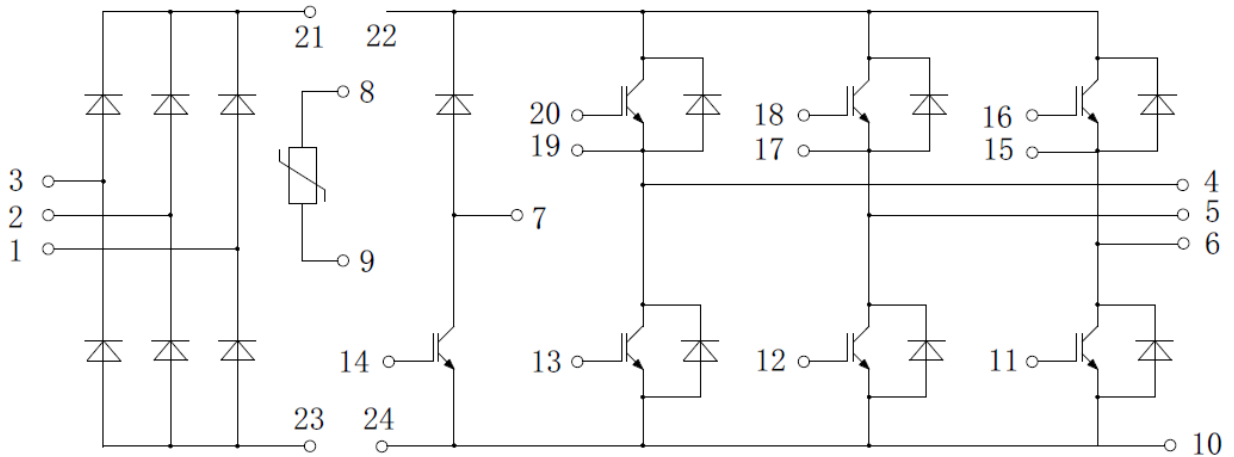




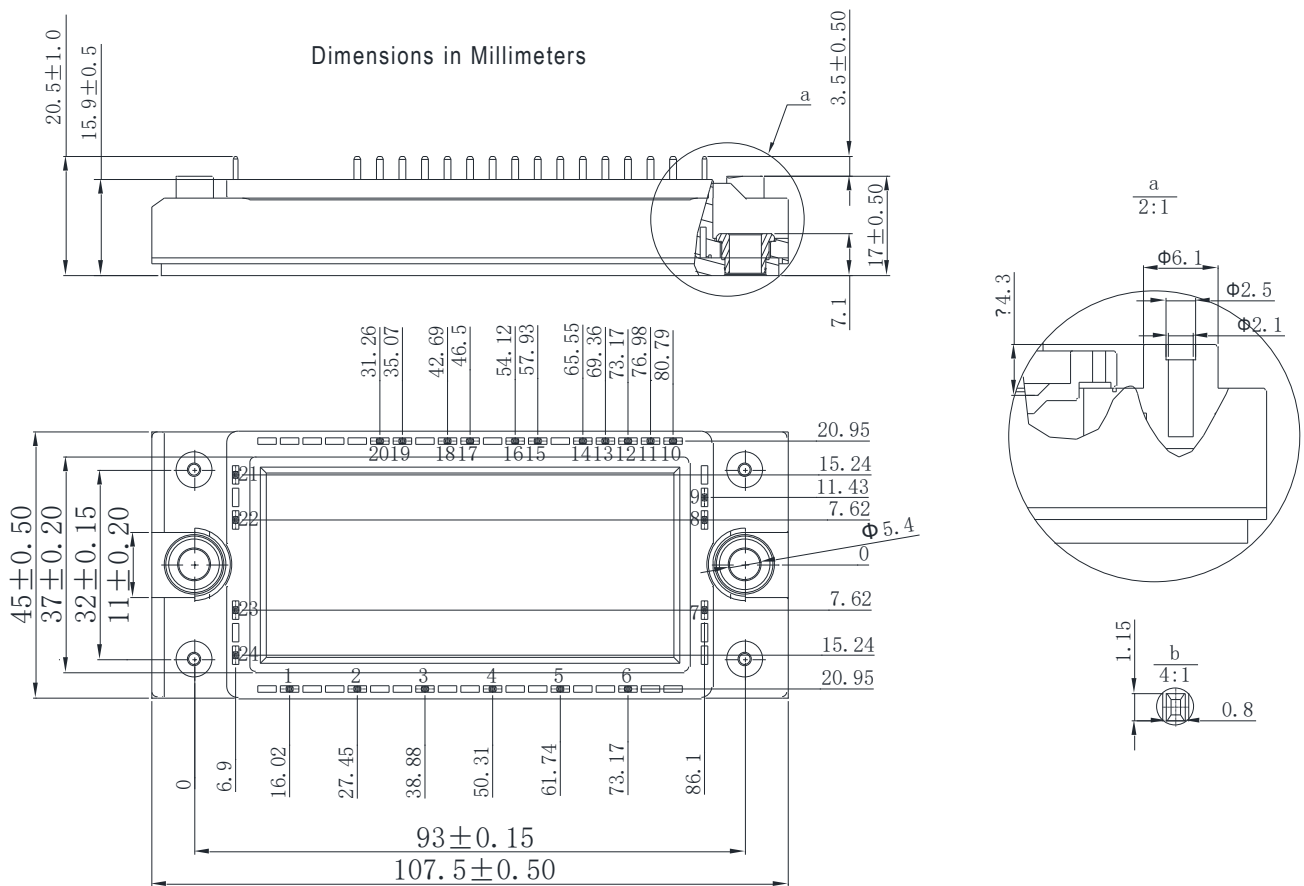




● **Circuit Diagram**



● **Package Dimensions**





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